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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	60	V
Gate-Source Voltage			V_{GSS}	±30	V
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	240 180	mA
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	0.5	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%) (Note 6)			I_{DM}	0.8	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_D	320	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	398	°C/W
Total Power Dissipation (Note 6)		P_D	470	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	273	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	V_{GS} = 0V, I_D = 10µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1.0	µA	V_{DS} = 60V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.0	—	2.5	V	V_{DS} = 10V, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	1.5 3.2	5.0 7.5	Ω	V_{GS} = 10V, I_D = 0.5A V_{GS} = 5V, I_D = 0.05A
Forward Transfer Admittance	$\|Y_{fs}\|$	80	—	—	mS	V_{DS} =10V, I_D = 0.2A
Diode Forward Voltage	V_{SD}	—	0.78	1.5	V	V_{GS} = 0V, I_S = 115mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	22	—	pF	V_{DS} = 25V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	4.1	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	2.5	—	pF	
Gate Resistance	R_g	—	120	—	Ω	f = 1.0MHz , V_{GS} = 0V, V_{DS} = 0V
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	361	—	pC	V_{GS} = 4.5V, V_{DS} = 10V, I_D = 250mA
Total Gate Charge (V_{GS} = 10V)	Q_g	—	821	—	pC	
Gate-Source Charge	Q_{gs}	—	162	—	pC	
Gate-Drain Charge	Q_{gd}	—	116	—	pC	
Turn-On Delay Time	$t_{D(ON)}$	—	2.8	—	ns	V_{DD} = 30V, I_D = 0.2A, R_L = 150Ω, V_{GS} = 10V, R_G = 25Ω
Turn-On Rise Time	t_R	—	3.0	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	7.6	—	ns	
Turn-Off Fall Time	t_F	—	5.6	—	ns	

Notes: 5. Device mounted on FR-4 PCB, with minimum recommended pad layout
6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

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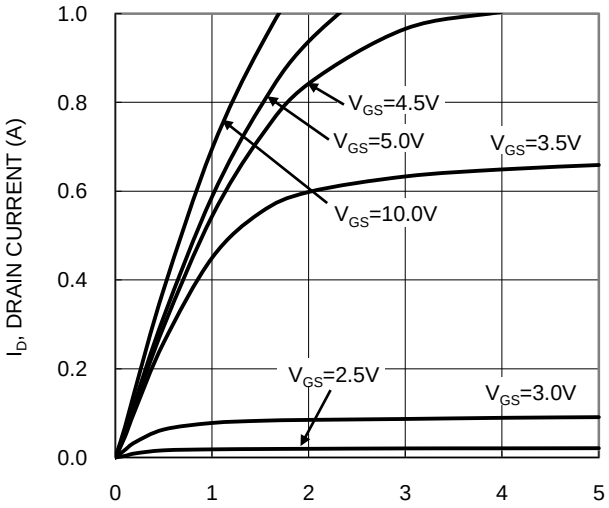

Figure 1. Typical Output Characteristic

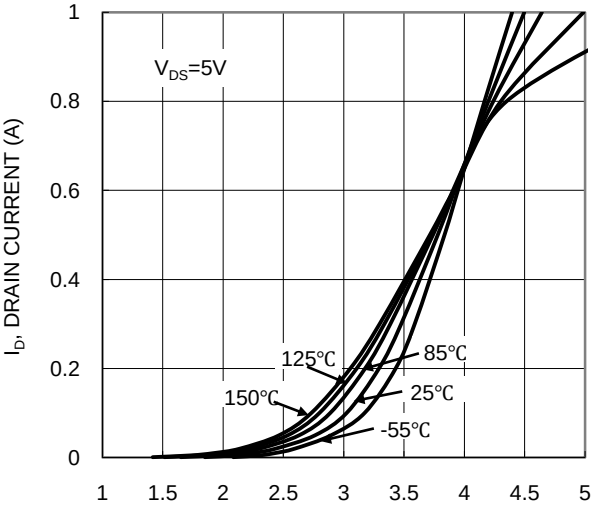

Figure 2. Typical Transfer Characteristic

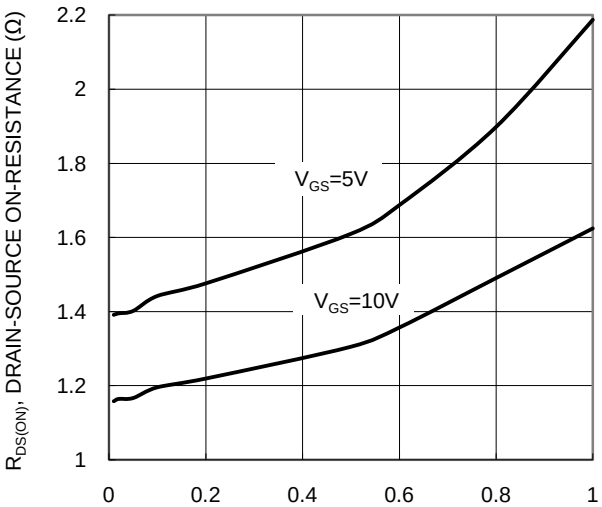

Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

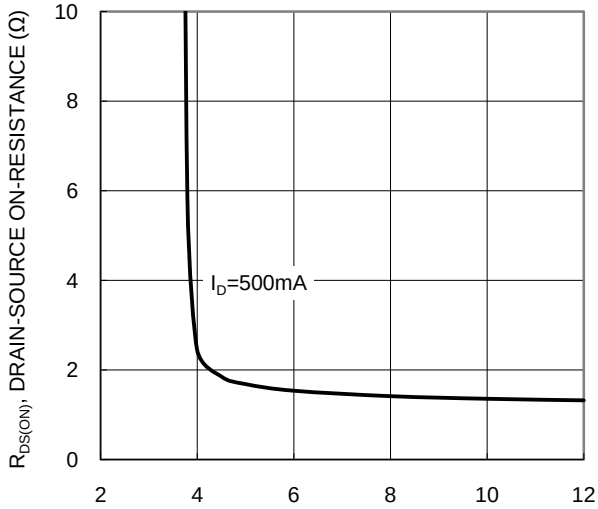

Figure 4. Typical Transfer Characteristic

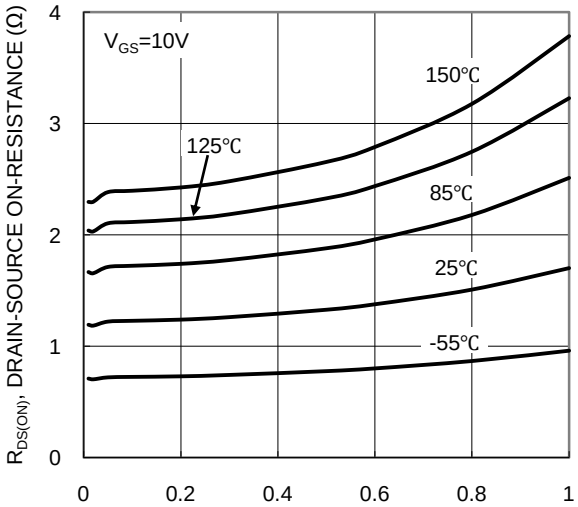

Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

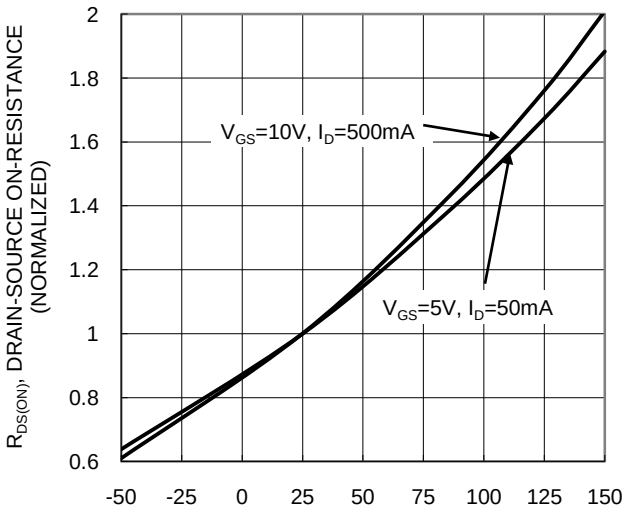

Figure 6. On-Resistance Variation with Junction Temperature

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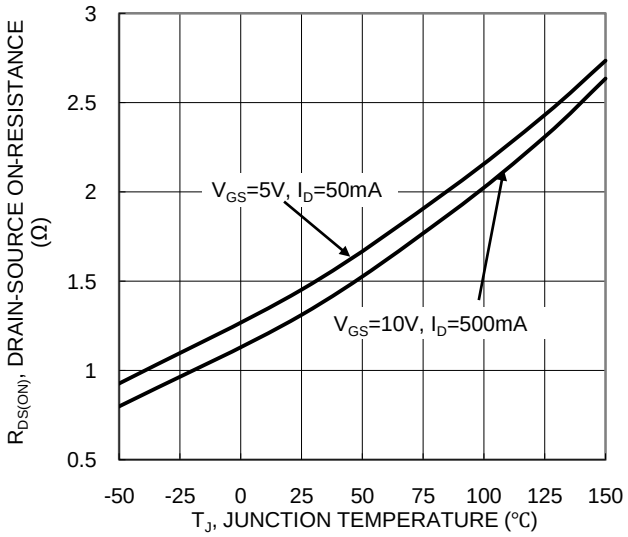

Figure 7. On-Resistance Variation with Junction Temperature

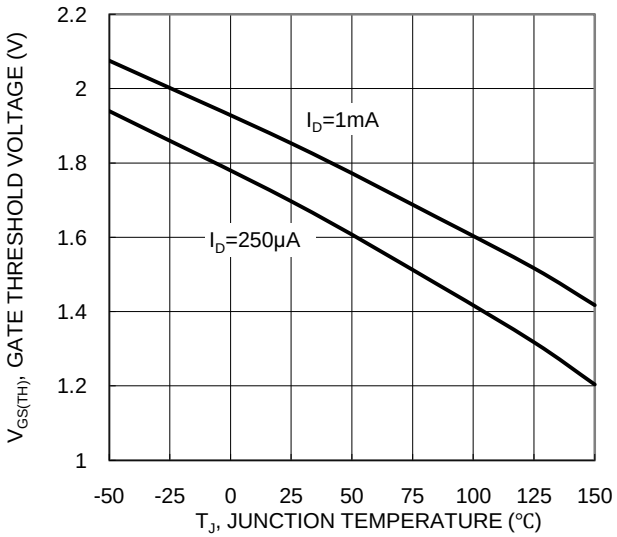

Figure 8. Gate Threshold Variation vs. Junction Temperature

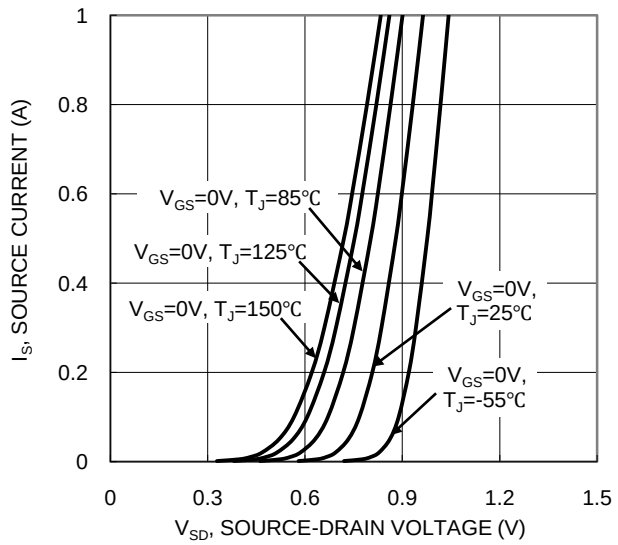

Figure 9. Diode Forward Voltage vs. Current

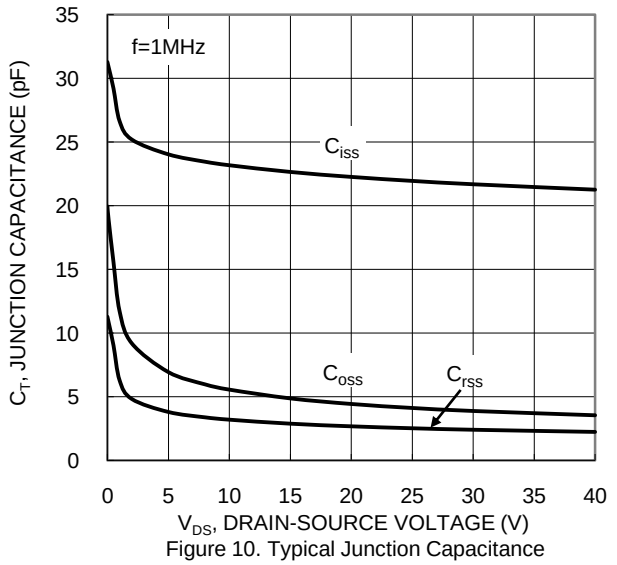

Figure 10. Typical Junction Capacitance

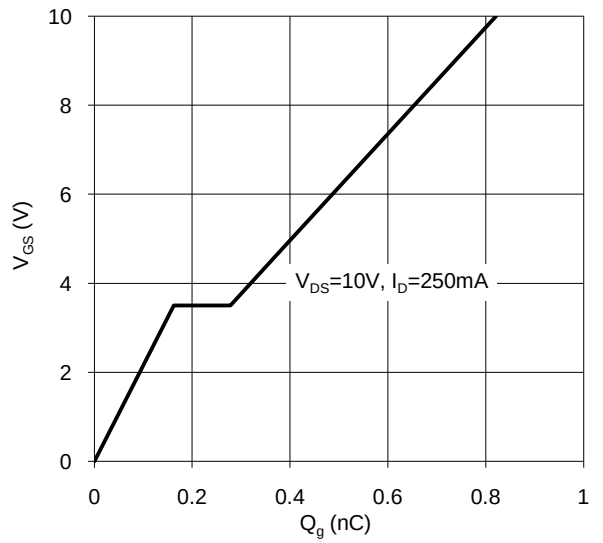

Figure 11. Gate Charge

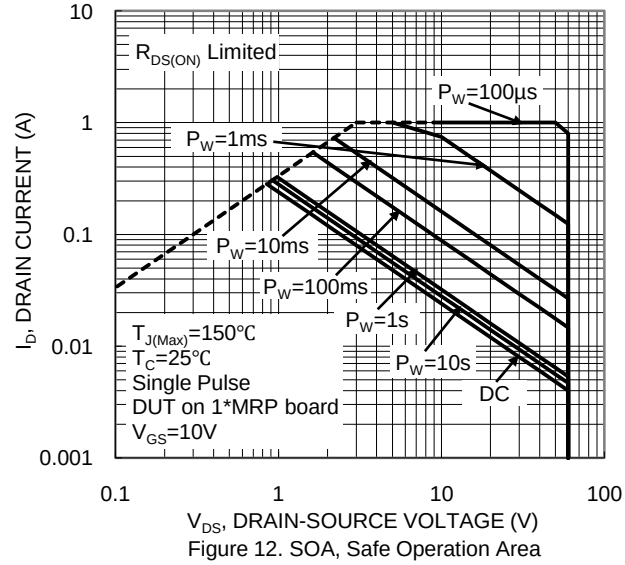

Figure 12. SOA, Safe Operation Area

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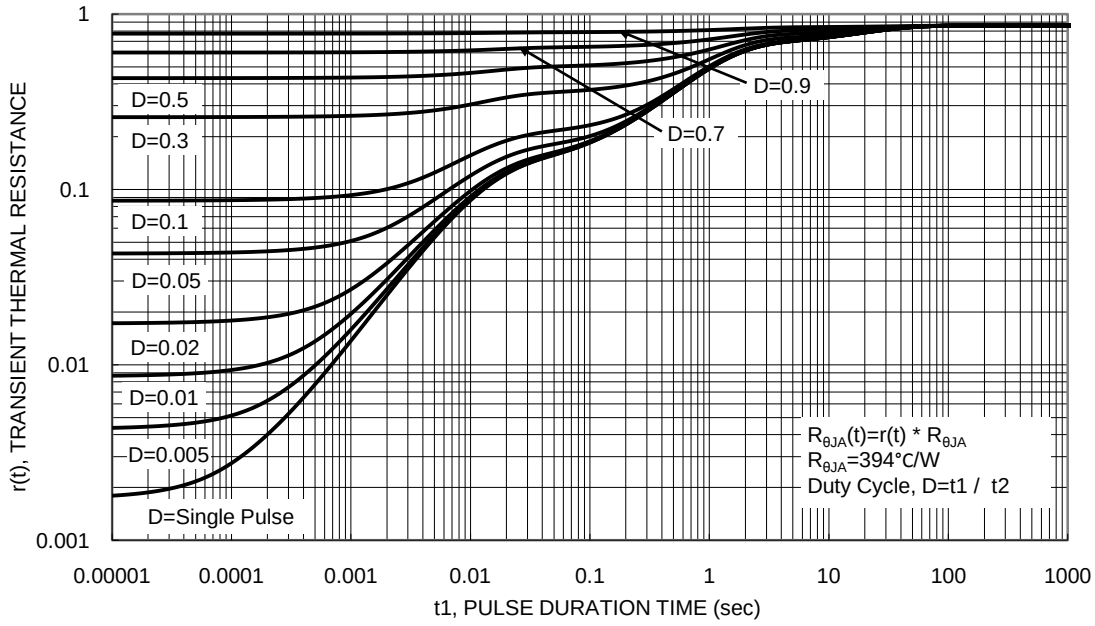
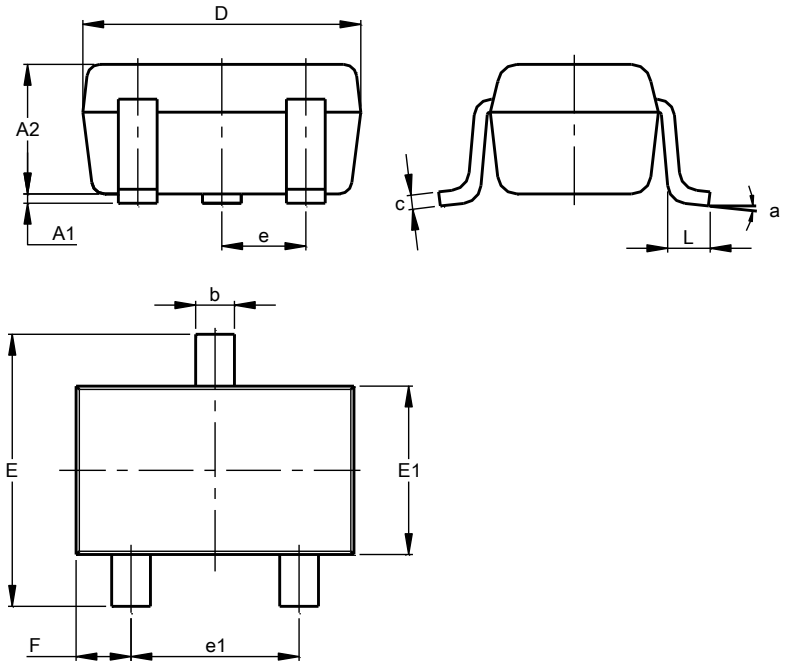


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT323			
Dim	**Min**	**Max**	**Typ**
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.25	0.40	0.30
c	0.10	0.18	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
e1	1.20	1.40	1.30
F	0.375	0.475	0.425
L	0.25	0.40	0.30
a	8°		
All Dimensions in mm			

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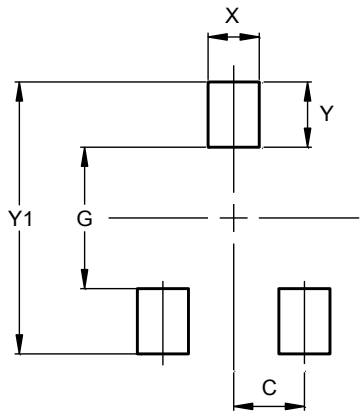
Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500